L Number	Hits	Search Text	DB	Time stamp
3	2	annealing with (substrate or wafer) with insulation with	USPAT;	2004/05/27 11:35
		(second adj side)	US-PGPUB;	,
			EPO; JPO;	
			DERWENT:	
			IBM TDB	
4	2	annealing same (substrate or wafer) same insulation same	USPAT;	2004/05/27 11:34
	-	(second adj side)	US-PGPUB	
		(,	EPO; JPO;	
			DERWENT:	
			IBM_TDB	
5	858	(anneal\$4 or (heat adj treatment)) same sublim\$5	USPAT;	2004/05/27 11:37
			US-PGPUB;	
			EPO; JPO;	
	]		DERWENT;	
			IBM_TDB	
6	1	(anneal\$4 or (heat adj treatment)) same sublim\$5 same	USPAT;	2004/05/27 11:50
•	·	(insulation adj film)	US-PGPUB;	2001100/21 11:00
		(modiation day min)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	66	(insulation adj film) with ((first or upper) adj side) with	USPAT;	2004/05/27 11:52
'		((second or buttom) adj side)	US-PGPUB;	200-700727 11.02
		((3000)14 or battorny day side)	EPO; JPO;	
			DERWENT;	
		·	IBM TDB	
9	0	(((insulation adj film) with ((first or upper) adj side) with	USPAT;	2004/05/27 11:54
•		((second or buttom) adj side)) and (etch\$4 with (first or	US-PGPUB;	2004/03/27 11.34
		upper))) and annneal\$5	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	47	((insulation adj film) with ((first or upper) adj side) with	USPAT;	2004/05/27 11:57
	''	((second or buttom) adj side)) and (etch\$4 with (first or	US-PGPUB;	2004/03/27 11.37
		upper))	EPO; JPO;	
		uppor//	DERWENT;	
			IBM_TDB	
10	35	sublimation with ((second or buttom) near3 substrate)	USPAT;	2004/05/27 12:05
'-		(coosing of partiern) hears superface)	US-PGPUB;	200-700727 12.00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	781	sublimation and 438.clas.	USPAT;	2004/05/27 13:00
`			US-PGPUB;	200-1700/21 10:00
			EPO; JPO;	
	ĺ		DERWENT;	
			IBM_TDB	
12	729	(sublimation and 438.clas.) and substrate	USPAT;	2004/05/27 12:57
<u> </u>		The state of the s	US-PGPUB;	
			EPO; JPO;	
	ĺ		DERWENT;	į
			IBM_TDB	
13	199	(sublimation with (substrate or wafer)) and 438.clas.	USPAT;	2004/05/27 13:01
		The state of training and toologo	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	'		IBM_TDB	
16	781	sublimation and 438/\$.ccls.	USPAT;	2004/05/27 13:01
			US-PGPUB;	_30 1/00/2/ 10.01
			EPO; JPO;	
	i		DERWENT;	
			IBM_TDB	

17	199	(sublimation with (substrate or wafer)) and 438/\$.ccls.	USPAT;	2004/05/27 13:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	,
			IBM TDB	
18	15	(sublimation with (substrate or wafer)) same insul\$5 and	USPAT;	2004/05/27 13:19
	1	438/\$.ccls.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	